

Automotive MOSFET Naming

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Product naming nomenclature



I: Infineon
AU: Automotive

Package Type
- A sTOLL
- A sTOLT top side cooled + suffix “T”
- C Single SSO8
- C Half-bridge in SSO8 + suffix “H”
- C Dual SSO8 + suffix “D”
- C Top Side Cooled SSO8 is SSO10T+ suffix “T”
- F SSO6
- M mTOLG + suffix "G"
- S TOLG
- T TOLG + suffix "G"
- S TOLT + suffix “T”
- T TOLT + suffix "T"
- T TOLL
- T Dual Gate in TOLL + suffix “L”
- Z S3O8

Channel
N: n-channel
P: p-channel

Continuous Drain Current I_{dmax} (A)
- *Not applicable after OptiMOS™ 7

Voltage class
- V_{DS} ÷10

Technology
- S7 OptiMOS™7
- S6 OptiMOS™6
- S5 OptiMOS™5
- P4 OptiMOS™P2

Gate threshold
- N: Normal Level
- L: Logic Level
- S: SOA Optimized

RDSon, max xx.x mΩ

Suffix of package type
- H Half-bridge
- T Top side cooling
- D Dual
- G Gullwings (mTOLG, TOLG)
- L Dual Gate

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Automotive MOSFET naming system

(used for up to OptiMOS™ 5 technology)



I → Infineon

Device:

P for Power MOSFET

Package Type:

B for TO263/D²PAK
C for SSO8 (TDSON-08)
D for TO252/DPAK
I for TO262/I²PAK
LU for TOLL (HSOF-8)
P for TO220
G for Dual SSO8 (TDSON-08)
Z for S3O8 (TSDSON-08)

Continuous drain current I_{Dmax}

P for P-channel
N for N-channel

Voltage V_{DS} ÷10

S for SFET1
S2 for OptiMOS™
S3 for OptiMOS™-T
S4 for OptiMOS™-T2
S5 for OptiMOS™-5
P3 for PFET3 Trench
P4 for PFET4 Trench

L for Logic Level
(no L is Normal Level)

$R_{DSon,max}$ in mΩ
"H" in front
for higher ohmic version
i.e. H5=5.5mΩ
"R" as decimal separator
i.e. 1R3=1.3mΩ

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